NSN 5962-01-506-2728

Memory Microcircuit - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5962-01-506-2728

| Maximum Power Dissipation Rating: |
|--|
| 1.0 watts |
| Operating Tempurature Range: |
| -55.0/+125.0 degrees celsius |
| Storage Tempurature Range: |
| |
| -65.0/+150.0 degrees celsius |
| End Application: |
| Alq135 band 1 |
| Inclosure Material: |
| Ceramic |
| Inclosure Configuration: |
| Leaded chip carrier |
| Output Logic Form: |
| Complementary-metal oxide-semiconductor logic |
| Current Rating Per Characteristic: |
| 20.00 milliamperes average forward current averaged over a full 60-hz cycle not applicable |
| Terminal Surface Treatment: |
| Solder |
| Product Name: |
| Microcircuit, digital, cmos, 2k x 9 first-in first-out, monolithic silicon |
| Voltage Rating And Type Per Characteristic: |
| -0.5 volts applied and 7.0 volts applied |
| Memory Device Type: |
| First-in first-out |
| Hybrid Technology Type: |
| Monolithic |
| Memory Capacity: |
| Cmos, 2k x 9 first-in, first-ou (fifo) |
| Terminal Type And Quantity: |
| 32 printed circuit |
| Shelf Life: |
| N/a |
| Unit Of Measure: |
| |
| Demilitarization: |
| Yes - demil/mli |
| Fiig: |
| A458a0 |
| |